MITSUBISHI SEMICONDUCTOR <GaAs FET>

MGFC39V5964A

5.9 ~ 6.4GHz BAND 8W INTERNALLY MATCHED GaAs FET

DESCRIPTION

The MGFC39V5964A is an internally impedance-matched GaAs power FET especially designed for use in 5.9 ~ 6.4 GHz band amplifiers. The hermetically sealed metal-ceramic package guarantees high reliability.

FEATURES

Class A operation Internally matched to 50(ohm) system High output power P1dB = 8W (TYP.) @ f=5.9~6.4GHz High power gain GLP = 10.5 dB (TYP.) @ f=5.9~6.4GHz High power added efficiency P.A.E. = 30 % (TYP.) @ f=5.9~6.4GHz Low distortion [item -51] IM3= -45 dBc(TYP.) @Po=28dBm S.C.L.

APPLICATION

item 01 : 5.9~6.4 GHz band power amplifier item 51: 5.9~6.4 GHz band digital radio communication

QUALITY GRADE

IG

1

RECOMMENDED BIAS CONDITIONS

VDS = 10 (V)ID = 2.4 (A)RG= 50 (ohm)

Refer to Bias Procedure

ABSOLUTE MAXIMUM RATINGS		(Ta=25 deg.C)	
Symbol	Parameter	Ratings	Unit
VGDO	Gate to drain voltage	-15	V
VGSO	Gate to source voltage	-15	V
ID	Drain current	7.5	Α
IGR	Reverse gate current	-20	mA
IGF	Forward gate current	42	mA
PT	Total power dissipation *1	42.8	W
Tch	Channel temperature	175	deg.C
Tstg	Storage temperature	-65 / +175	deg.C
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*1 : Tc=25 deg.C

Symbol

VGS(off)

IDSS

P1dB

GLP

P.A.E

IM3

ID

gm

ELECTRICAL CHARACTERISTICS

Power added efficiency

3rd order IM distortion

(Ta=25 deg.C) Limits Parameter Test conditions Unit Min. Тур. Max. Saturated drain current VDS=3V, VGS=0V 7.5 А -Transconductance VDS=3V, ID=2.2A _ 2 S Gate to source cut-off voltage VDS=3V, ID=20mA -4.5 V Output power at 1dB gain compression 38 39.5 dBm Linear power gain VDS=10V, ID(RF off)=2.4A, f=5.9~6.4GHz 8 10.5 dB _ Drain current 3 А

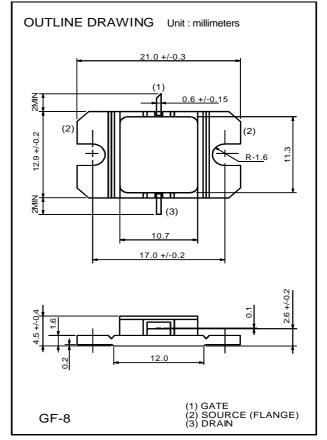
*2 Delta Vf method Thermal resistance Rth(ch-c)

1 : item -51, 2 tone test, Po=28dBm Single Carrier Level, f=6.4GHz, Delta f=10MHz

*1

*2 : Channel to case





%

dBc

deg.C/W

30

-45

-42

-

3.5

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